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Electronic emission spectroscopy of Group IV tetrachloro molecular ions

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Two broad continuous bands are observed in the visible region following electron impact ionization of a He-seeded molecular beam of SiCl₄ or GeCl₄. By using tunable vacuum UV radiation from a synchrotron source to measure the threshold energy at which the fluorescence bands occur, it is shown that the bands are related to the initial formation of the $\tilde{C}^2 T_2$ state of the parent ion SiCl₄⁺/GeCl₄⁺. By comparison with photoelectron data, the bands are assigned to bound-free transitions in SiCl₄⁺/GeCl₄⁺ $\tilde{C}^2 T_2 - \tilde{A}^2 T_2$ and $\tilde{X}^2 T_1$. The \tilde{C} state of CCl₄⁺ does not fluoresce. The results are compared with the electronic emission spectra of the three tetrafluoro molecular ions.

I. INTRODUCTION

In a series of papers, 1-3 two of us have reported observation of electronic emission spectra of three Group IV tetrafluoro molecular ions CF_4^+ , SiF_4^+ , and GeF_4^+ in the gas phase. The spectra are observed at a low rotational temperature in a crossed molecular beam/electron beam apparatus. For all three ions both continuous and discrete bands have been observed in the visible-UV region of the electromagnetic spectrum. From photoelectron spectroscopy, the ground and first two excited electronic states $(\tilde{X}, \tilde{A}, \text{ and } \tilde{B})$ of MF_4^+ known to dissociate rapidly to $MF_3^+ + F$ are (M = C,Si,Ge), and the continuous bands arise from transitions to these states. These three states arise from electron removal from molecular orbitals in MF₄ which are essentially F 2p nonbonding in character. The third and fourth excited electronic states (\tilde{C} and \tilde{D}) of CF_4^+ and SiF_4^+ give vibrational structure in their photoelectron spectra,⁴⁻⁶ and hence are bound; these states of GeF_4^+ are also bound, but the vibrational structure is unresolved.³ They arise from electron removal from t_2 and a_1 molecular orbitals in MF₄ that are essentially bonding in character. These are the upper states of the bound-free continuous transitions (e.g., CF₄⁺ \tilde{C} - \tilde{A} at 290 nm, SiF₄ + \tilde{D} - \tilde{A} at 304 nm, and GeF₄ + \tilde{D} - \tilde{A} at 255 nm).⁷⁻⁹ The discrete bands arise from an allowed transition between the two bound states $\tilde{D}^2 A_1 - \tilde{C}^2 T_2$, and this spectrum is described in detail in Refs. 1-3. From a spectroscopic point of view, interest has concentrated on the triply degenerate $\tilde{C}^2 T_2$ state of these ions which show spin-orbit splitting, Coriolis splitting, and in SiF_4^+ and $GeF_4^{+2,3}$ distortion from tetrahedral geometry via the Jahn-Teller effect. From a dynamics point of view, the interest is to understand why these excited electronic states fluoresce at all. They lie up to 10 eV above the lowest ionic dissociation channel,¹⁰ and such states might be expected to decay nonradiatively rather than by a radiative channel. The observation of fluorescence decay from highly excited electronic states of these polyatomic ions is therefore a very surprising phenomenon.

In this paper we describe experiments to observe electronic emission spectra of the complementary Group IV tetrachloro molecular ions CCl_4^+ , $SiCl_4^+$, and $GeCl_4^+$. Three

different methods of ionization are used: nonselective electron impact ionization, Penning ionization using He* and Ne* metastables, and photoionization using tunable VUV radiation from the synchrotron storage ring at the SERC Daresbury Laboratory. No discrete bands are observed, but broad band (bound-free) transitions are observed with SiCl₄ and GeCl₄. The experiments confirm that these bands are due to fluorescence decay from the bound C^2T_2 state of the parent ion to lower-lying repulsive electronic states. The $\tilde{D}^2 A_1$ states of SiCl₄⁺ and GeCl₄⁺ do not fluoresce, and neither \tilde{C} nor \tilde{D} of CCl⁺₄ show fluorescence decay. These experiments are spectroscopic in nature, as the aim is to discover the emitter of particular fluorescence band systems. In the following paper we describe dynamic experiments to measure fluorescence quantum yields and radiative lifetimes of the fluorescing states of MF_4^+ and MCl_4^+ .

II. EXPERIMENTAL

The electron impact and Penning ionization experiments were performed in Birmingham. The crossed molecular beam-electron beam apparatus has been described in detail elsewhere.¹¹ A rotationally cold supersonic beam of the appropriate tetrachloride seeded in helium is formed by expansion of the gas mixture through a 100 μ m stainless-steel nozzle, collimated by a 0.5 mm diameter skimmer (Beam Dynamics Inc.), and crossed by an electron beam with an energy of approximately 200 eV and a beam current of 5-10 mA. It is noted that this method of ionization generally has a high cross section, but is not energy selective. Fluorescence from the crossing region is dispersed by a 1.26 m f/9 scanning monochromator (Spex 1269) equipped with a holographic grating (1800 ℓ mm⁻¹) and a cooled RCA C31034 pm tube connected with single photon counting electronics. This detector has a uniform response between 300 and 830 nm. The scanning of the monochromator and fluorescence collection are controlled by a BBC microcomputer, and data is transferred to the University Mainframe Computer (Honeywell DPS-8/70M) for analysis. It is noted that in this apparatus a discrete spectrum of the parent molecular ion will be observed at a low rotational temperature, 1-3,11 but a broad band bound-free spectrum will not be affected by the reduced temperature of the emitter. CCl_4 , $SiCl_4$, and $GeCl_4$ are all volatile liquids at room temperature, and the expansion mixture is obtained by passing helium over the liquid surface in a glass container outside the vacuum (nozzle) chamber. The liquids are used at 298 K, and the pressure of helium is typically 1 atm.

SiCl₄ and GeCl₄ were studied further in Birmingham by Penning ionization. Rare gas metastables A^* (A = He and Ne) produced in a microwave discharge are used to ionize SiCl₄/GeCl₄ at room temperature. For example,

$$\mathbf{A^*} + \operatorname{SiCl}_4 \to \mathbf{A} + \operatorname{SiCl}_4^+ + e^-$$

The total pressure is 15–20 Torr. Emitted light is focused onto the entrance slit of a 0.3 m f/5 scanning monochromator (Hilger and Watts), dispersed by a 600 ℓ mm⁻¹ grating blazed at 300 nm, and detected by an EMI 9635 QB pm tube used at room temperature in the dc mode. Experiments with two rare gas metastables He* and Ne* (excitation energies 19.82 and 16.72 eV, respectively) were performed. The cross sections for Penning ionization generally are smaller than for 200 eV electron impact ionization, but by varying the rare gas there is a limited degree of energy selectivity in the ionization process.

In the third experiment, a photoionization method is used to ionize CCl₄, SiCl₄, and GeCl₄ at room temperature, using tunable VUV radiation in the energy range 12-35 eV (100-35 nm) from the synchrotron storage ring at the SERC Daresbury Laboratory. This experiment is described in detail in the following paper. Briefly, an effusive spray of pure MCl₄ vapor at a pressure of $\sim 10^{-4}$ Torr is crossed by tunable VUV radiation dispersed from a 1 m VUV Seya monochromator. The photon flux in the apparatus is measured by an Al₂O₃ photocathode. Fluorescence from the ions initially produced or from fragment species is collected simultaneously by two pm tubes (an uncooled EMI 9883 QB and a red-enhanced Mullard 2254 with an S20 photocathode cooled to -20 °C) through optical filters. The signals are detected by single photon counting electronics. The scanning of the Seya monochromator, the recording of the incident photon flux and fluorescence collection are computer controlled, and data is transferred to the Daresbury Mainframe Computer (AS7000) for analysis.

III. ENERGETICS OF THE IONIC STATES OF MCI4 AND DISSOCIATION CHANNELS

The description of the valence molecular orbitals in MCl_4 is very similar to that given for the tetrafluorides MF_4 in Sec. I. The valence molecular orbitals now arise from overlap of the 16 chlorine atom valence orbitals $Cl_{3s,3p}$ with the central atom valence orbitals (e.g., $C_{2s,2p}$). The central atom d orbitals have only a secondary role in the bonding. The electron configuration corresponding to the five highest occupied molecular orbitals of neutral MCl_4 is \cdots $(2a_1)^2(2t_2)^6(1e)^4(3t_2)^6(1t_1)^6$. The labeling used does not include core orbitals in the numbering scheme. He I and He II photoelectron (PE) spectroscopy show that five electronic states of the mono-positive ion MCl_4^+ exist below 21.2 eV, $^{12-14}\tilde{X}^2T_1$, \tilde{A}^2T_2 , \tilde{B}^2E , \tilde{C}^2T_2 , and \tilde{D}^2A_1 , corresponding

to electron removal from the $1t_1$, $3t_2$, 1e, $2t_2$, and $2a_1$ molecular orbitals, respectively. This assignment for the molecular orbital sequence also agrees with theoretical calculations.^{15,16} Vibrational structure has only been resolved in the fifth band of SiCl₄ (ionization to $\tilde{D}^2A_1:v_1 \simeq 290 \text{ cm}^{-1}$ ¹⁴), although Jahn–Teller and spin–orbit splittings are apparent in several other PE bands. However, it is noted that in the fourth PE band (ionization to \tilde{C}^2T_2) neither spin–orbit splitting nor Jahn–Teller splitting is observed in CCl₄⁺, SiCl₄⁺, or GeCl₄⁺.

The three highest molecular orbitals 1e, $3t_2$, and $1t_1$ are all nonbonding and composed mainly of pure chlorine 3patomic orbitals. The $2t_2$ and $2a_1$ orbitals are largely the bonding orbitals between the chlorine atoms and the central atom. $2t_2$ is the bonding orbital between the valence p orbitals of the central atom and the 3p valence orbitals of the chlorine atoms. The bonding orbital $2a_1$ has s character of the central atom and 3s/3p character of the chlorine atoms. Semiempirical MNDO molecular orbital calculations¹⁷ show that it is incorrect to label the $3t_2$ and $2t_2$ orbitals as π nonbonding and σ bonding where the Cl 3p orbitals are aligned perpendicular to and parallel to the M-Cl bonds, respectively. Both $3t_2$ and $2t_2$ are a mixture of σ - and π -type orbitals, and this is reflected in the magnitude and sign of the spin-orbit splitting constant in $MCl_4^+ \tilde{A}^2T_2$ and \tilde{C}^2T_2 .¹⁷

The vertical ionization potentials (IPs) of these five ionic states of CCl_4^+ , $SiCl_4^+$, and $GeCl_4^+$ taken from Ref. 12 are given in Table I, together with the energies of some of the neutral and ionic dissociation channels. The energies of the neutral dissociation channels of CCl₄ and SiCl₄ come from well-established heats of formation.^{22,23} The energies of the GeCl₄ channels (e.g., GeCl₄ \rightarrow GeCl₂ + Cl₂) come from several sources and are probably less accurate.²⁴⁻²⁶ The energies of the ionic fragments (e.g., $SiCl_4 \rightarrow SiCl_3^+ + Cl$) come from adding the appropriate neutral energy to the ionization potential (IP) of the fragment (SiCl₃ in this case). The IPs of MCl_n (n = 1-3) come from a variety of sources. A photoelectron spectrum, a direct electron impact measurement, or an analysis of the Rydberg series of the parent molecule/ radical give the most accurate data. Thus the IP of CCl is 8.9 eV,²⁷ CCl₂ 9.8 eV,²⁸ SiCl 6.8 eV,²⁹ SiCl₂ 10.1 eV,³⁰ GeCl 7.2 eV³¹ and $GeCl_2$ 10.2 eV^{32} ; the photoelectron values^{30,32} are adiabatic IPs. The CCl₃, SiCl₃, and GeCl₃ free radicals are short lived, and no direct measurement of their IPs have been made. Data is only available from appearance potentials of MCl_3^+ from MCl_4 , and this will give an upper limit to the IP of MCl₃. Thus we use IP values of 8.8, 7.9, and 9.5 eV for CCl₃, SiCl₃, and GeCl₃, respectively.^{25,33,34}

Since some of the thermodynamic data and IP measurements are quite old, we quote only one decimal point in the energies of the dissociation channels in Table I, although the energies of some channels are more accurately known. Two particular points about these energetics are worth noting. First, for all three Group IV tetrachlorides the MCl₃⁺ + Cl threshold lies close to the ground electronic state of MCl₄⁺, and in fact the MCl₃⁺ ion is the strongest peak in the mass spectrum cracking pattern of MCl₄.³⁵ Second, there are a number of dissociation channels energetically "open" to the $\tilde{C} {}^2T_2$ and $\tilde{D} {}^2A_1$ states of the parent ion, and therefore any

TABLE I. Energetics of dissociation channels of MCl_4 and MCl_4^+ (M = C,Si,Ge) in eV.

Neutral/parent ion	Dissociation channel	Energy
		(eV) ^a
	$CCl + Cl^+ + Cl_2$	20.4
$\operatorname{CCl}_4^+ \widetilde{D}^2 A_1$		20.4 ^b
~~~~	$CCl + Cl + Cl_2^+$	18.9
$\tilde{C}^2 T_2$		16.68
	$CCl^+ + Cl + Cl_2$	16.3
	$CCl_3 + Cl^+$	16.0 15.0
$\widetilde{B}^{2}E$	$\mathrm{CCl}_2 + \mathrm{Cl}_2^+$	13.37
B L	$\operatorname{CCl}_2^+ + \operatorname{Cl}_2$	13.37
$\tilde{A}^2 T_2$	$\operatorname{ccl}_2 + \operatorname{cl}_2$	12.51
A 12	$CCl_3^+ + Cl$	11.8
$\operatorname{CCl}_4^+ \widetilde{X}^2 T_1$		11.64
	$CCI + CI + CI_2$	7.4
	$\operatorname{CCl}_2 + \operatorname{Cl}_2$	3.5
	$CCl_3 + Cl_2$ $CCl_3 + Cl$	3.0
$\operatorname{CCl}_{4}\widetilde{X} {}^{I}A_{1}$		0
		<b>aa</b> -
	$SiCl + Cl^+ + Cl_2$	23.0
S. S. 1	$SiCl + Cl + Cl_2^+$	21.5
$\operatorname{SiCl}_{4}^{+} \widetilde{D}^{2}A_{1}$	a	18.10
	$SiCl_3 + Cl^+$	17.8
	$SiCl^+ + Cl + Cl_2$	16.8
$\tilde{C}^2 T_2$	$SiCl_2 + Cl_2^+$	16.6
$C^{-1}$	$SiCl_2^+ + Cl_2$	15.27 15.2
$\widetilde{B}^{2}E$	$\operatorname{SiCl}_2 + \operatorname{Cl}_2$	13.51
$\tilde{A}^{2}T_{2}$		13.03
A 12	$SiCl_{3}^{+} + Cl$	12.7
$SiCl_4^+ \tilde{X}^2 T_1$		12.12
	$SiCl + Cl + Cl_2$	10.0
	$SiCl_2 + Cl_2$	5.1
	$SiCl_3 + Cl$	4.8
$SiCl_4 \widetilde{X}  {}^{I}A_1$		0
		20.0
	$GeCl + Cl^+ + Cl_2$	20.9
$\operatorname{GeCl}_{4}^{+} \widetilde{D}^{2}A_{1}$	$GeCl + Cl + Cl_2^+$	19.4
$\operatorname{GeCl}_4^{-1} D^{-1}A_1$	$\alpha \alpha + \alpha +$	18.38
	$GeCl_3 + Cl^+$ $GeCl^+ + Cl + Cl_3$	15.8
$\tilde{C}^2 T_2$	$\mathbf{U}_{\mathbf{U}_1} + \mathbf{U}_1 + \mathbf{U}_2$	15.1 14.88
	$\operatorname{GeCl}_2 + \operatorname{Cl}_2^+$	14.88
	$\operatorname{GeCl}_2^+ + \operatorname{Cl}_2$ $\operatorname{GeCl}_2^+ + \operatorname{Cl}_2$	13.5
$\tilde{B}^{2}E$		13.05
$\tilde{A}^2 T_2$		12.64
2	$\text{GeCl}_3^+ + \text{Cl}$	12.3
$\operatorname{GeCl}_{4}^{+} \widetilde{X}^{2}T_{1}$	, ,	12.17
	$GeCl + Cl + Cl_2$	7.9
	$\operatorname{GeCl}_2 + \operatorname{Cl}_2$	3.3
	$GeCl_3 + Cl_2$	2.8
GeCl₄X 'A		0

^a In addition to the thermodynamic and IP data in the text, we use  $IP(Cl_2) = 11.5 \text{ eV}$  (Ref. 18), IP(Cl) = 13.0 eV (Ref. 19), and  $D_0^0$  (Cl-Cl) = 2.5 eV (Ref. 20). ^b Reference 21.

fluorescence decay from these states is a surprising phenomenon.

#### **IV. RESULTS**

The emission spectra resulting from electron impact on supersonic beams of  $SiCl_4$  and  $GeCl_4$  seeded in helium are shown in Figs. 1 and 2. The optical resolution is 0.2 nm. The

SiCl₄ spectrum (Fig. 1) between 350 and 670 nm shows no discrete molecular structure, but consists of two broad structureless bands with maxima at 410 and 570 nm. In addition there are many narrow atomic lines (assigned to Si, Cl, He, or N atomic transitions), and strong  $N_2^+$  B-X bands at 391 nm(0,0) and 428 nm (0,1) from residual nitrogen in the apparatus. The GeCl₄ emission spectrum (Fig. 2) is very similar in appearance to the SiCl₄ spectrum. It consists of two continuous bands with maxima at 495 and 615 nm, and many narrow atomic lines due to Ge, Cl, He, or N. The  $N_2^+$ B-X(0,1) band again is present. It is noted that the response of the RCA C31034 pm tube used is essentially flat over the spectral range 300-830 nm, and therefore no correction needs to be made to the observed fluorescence intensities in this region. The emission spectrum resulting from electron impact on a CCl₄/He supersonic beam was also recorded between 300 and 830 nm. No discrete or continuous bands could be identified above the noise from the electron gun filament, although many atomic lines are observed.

The emission spectra resulting from rare gas metastables impacting on SiCl₄ and GeCl₄ at room temperature have been recorded between 350 and 700 nm in the Penning ionization apparatus. Having corrected for the changes in grating efficiency and photomultiplier response over this wide range, with both He* and Ne* metastables both SiCl₄ and GeCl₄ give spectra very similar to those observed in the molecular beam/electron beam apparatus (Figs. 1 and 2). An initial experiment with N₂ showed that no species from the neon discharge had sufficient excitation energy to produce  $N_2^+ B^2 \Sigma_u^+$  ions (at 18.7 eV), since no  $N_2^+ B - X$  fluorescence at 391 nm was observed. This suggests that the neon discharge only produces Ne*  ${}^{3}P_{2}$  and  ${}^{3}P_{0}$  metastables with energies of 16.62 and 16.72 eV, respectively. By contrast, intense  $N_2^+$  B-X fluorescence is observed with a helium discharge, confirming that this discharge produces helium metastables with an energy greater than 18.7 eV (i.e., He^{*3}S with energy 19.82 eV). These experiments show that the emitting state of the emission bands in SiCl₄/GeCl₄ is related to the formation of an excited state with energy less than 16.62 eV above the ground state of  $SiCl_4/GeCl_4$ .

The results of the synchrotron-induced fluorescence experiments on SiCl₄ and GeCl₄ are shown in Figs. 3 and 4. Figure 3 shows the total undispersed fluorescence collected in the range 320-470 nm (EMI 9883 QB pm tube + Wratten 35 filter) when SiCl₄ is excited by VUV radiation with energy in the range 14-35 eV (i.e., 88-35 nm). The resolution of the Seya monochromator is 0.2 nm. The fluorescence signal has been normalized to photon flux, and full details are given in the following paper. Undispersed fluorescence is collected simultaneously in the range 505-750 nm (Mullard 2254 pm tube + Schott OG515 cut-on filter), and the fluorescence spectrum is identical to Fig. 3. These two wavelength ranges span the two broad bands observed in the molecular beam/ electron beam apparatus, so the fluorescence function in Fig. 3 indicates the excitation energy at which the two continuous bands first appear. For SiCl₄, this energy is  $15.1 \pm 0.1$ eV. The fluorescence spectrum shows a sharp increase at this threshold, and some weak structure between 16.5 and 18.0 eV (see Sec. V C). It is noted (Table I) that the vertical

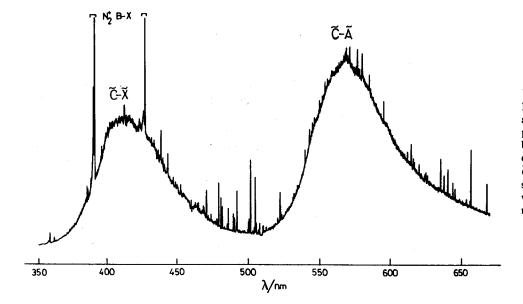


FIG. 1. Emission spectrum between 350 and 670 nm resulting from electron impact ionization of a He-seeded supersonic beam of SiCl₄. The continuous bands are due to emission of SiCl₄⁺ from the bound  $\tilde{C}^2T_2$  state to repulsive  $\tilde{A}^2T_2$  and  $\tilde{X}^2T_1$ states. The sloping background as the wavelength increases is due to increasing noise from the electron gun filament.

#### ionization potentials of SiCl₄⁺ $\tilde{C}^2 T_2$ and $\tilde{D}^2 A_1$ are 15.27 and 18.10 eV, respectively¹²; the adiabatic ionization potential of $\tilde{C}$ ² $T_2$ is 15.09 eV.¹² Figure 4 shows the result of the same experiment with GeCl₄, fluorescence being collected in the range 410-600 nm (EMI 9883 QB pm tube + Oriel LF42 cut-on filter). An identical fluorescence spectrum is obtained when fluorescence in the range 560-750 nm is collected (Mullar 2254 pm tube + Schott OG570 cut-on filter). These two spectral regions are approximately the same as those covered by the two continuous bands in the molecular beam/electron beam experiment with GeCl₄. The fluorescence function shows a sharp increase at $14.5 \pm 0.1$ eV, and we note that the adiabatic ionization potential of GeCl⁺ $\tilde{C}^2 T_2$ is 14.56 eV.¹² The fluorescence spectrum of CCl₄ was also studied in the energy range 14-35 eV (88-35 nm). Fluorescence is collected in the range 410-750 nm by the cooled Mullard 2254 pm tube + Oriel LF42 cut-on filter. Over this range of the synchrotron energy there is a very weak fluorescence signal (which is proportional to the synchrotron flux) detectable above the dark count of the pm tube, but no sharp turn on in the fluorescence is observed (as with SiCl₄ and GeCl₄).

#### **V. ASSIGNMENT OF SPECTRA**

The results reported in Sec. IV complement two other recent ionization studies on Group IV tetrachlorides. van Lonkhuyzen and Aarts³⁶ have observed the emission spectra produced by 1-25 keV H⁺ impact on CCl₄, SiCl₄, and GeCl₄ at room temperature. The spectra are very similar to those observed in the molecular beam/electron beam apparatus: no discrete or continuous bands are observed with CCl₄, whereas the SiCl₄ and GeCl₄ spectra comprise two broad bands with the same maxima and spectral ranges as shown in Figs. 1 and 2. van Lonkhuyzen and Aarts measured the dependence of the cross section for fluorescence as a function of ion beam energy (cf. similar experiments on CF₄, SiF₄, and  $GeF_4^{7-9}$ ), but unfortunately they were unable to determine any information about the states of the ions initially formed in the excitation process. Toyoda et al.37 have observed the emission spectra of MCl₄ under controlled electron impact excitation (300 eV) at 300 K. The SiCl₄ and GeCl₄ emission spectra are the same as those shown in Figs. 1 and 2, but the  $CCl_4$  spectrum shows a single broad band with a maximum at 480 nm. The latter band was assigned to CCl₂, while the broad bands in the SiCl₄ and GeCl₄ spectra

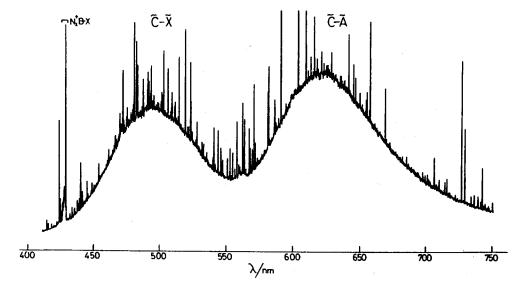


FIG. 2. Emission spectrum between 410 and 750 nm resulting from electron impact ionization of a He-seeded supersonic beam of GeCl₄. The continuous bands are due to emission of GeCl₄⁺ from the bound  $\tilde{C}^2T_2$  state to repulsive  $\tilde{A}^2T_2$  and  $\tilde{X}^2T_1$  states.

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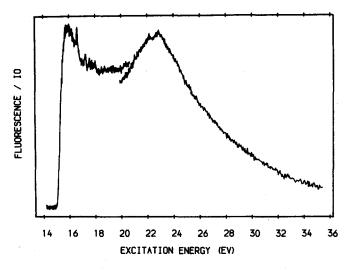


FIG. 3. Undispersed fluorescence of SiCl₄ excited by VUV radiation in the range 14–35 eV. The spectrum was recorded in two overlapping sections. Only photons in the range 320–470 nm are detected, and the photon count rate has been normalized to the synchrotron flux  $I_0$ .

were tentatively assigned to  $SiCl_2$  and  $GeCl_2$ , respectively. We note that the gas pressure in these experiments is relatively high, and therefore the spectra are probably not being observed under single-collision conditions.

Thus the emission bands obtained with SiCl₄ and GeCl₄ in Figs. 1 and 2 are observed with several different ionization techniques ( $e^-$  impact, fast H⁺ impact, Penning ionization, photoionization). In each technique the experimental conditions strongly favor the formation of ions. For example, experience on the molecular beam/electron beam apparatus has shown that the observation of emission from excited electronic states of the parent neutral molecule is rare.³⁸ Instead, emission from excited states of the parent molecular ion (or fragments) is usually seen. It is therefore instructive to compare these optical emission spectra with photoelectron data for SiCl₄ and GeCl₄. Table II shows calculated wavelengths for the band maxima of the transitions SiCl₄⁺ and GeCl₄⁺  $\tilde{C}^2 T_2 - \tilde{A}^2 T_2$  and  $\tilde{C}^2 T_2 - \tilde{X}^2 T_1$  as obtained from

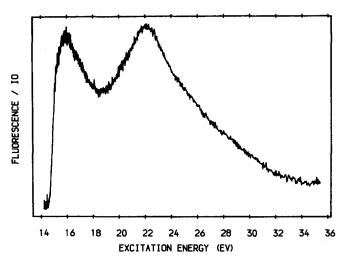


FIG. 4. Undispersed fluorescence of GeCl₄ excited by VUV radiation in the range 14–35 eV. The spectrum was recorded in two sections. Only photons in the range 410–600 nm are detected, and the photon count rate has been normalized to the synchrotron flux  $I_0$ .

TABLE II. Calculated wavelengths for transitions in SiCl₄⁺ and GeCl₄⁺ as deduced from photoelectron data. The observed maxima of emission bands resulting from electron impact on SiCl₄ and GeCl₄ are included for comparison. Wavelengths in nm.

	Transition	PE data ^a	e ⁻ impact
SiCl ₄ ⁺	Č-X	394	410
	Č-Ă	553	570
GeCl ₄ +	Č−X̃	458	495
	Ĩ-Ã	554	615

* Vertical IP data from Table I, i.e., Ref. 12.

differences between vertical IPs. It is noted that the band maximum for a transition from a bound to a dissociative electronic state of an ion can only be estimated in this way. Nevertheless, the predicted wavelengths for the band maxima fall within 0.2 eV of the observed positions, but all at a lower value. This same pattern is observed in  $CF_4^+ C - A, X$ emission (Table I of Ref. 7), and furthermore this latter spectrum (Fig. 1 of Ref. 7) is remarkably similar to that found for electron impact on SiCl₄/GeCl₄: it consists of two broad structureless bands with the higher wavelength band (C-A) being of slightly greater intensity. This analysis therefore suggests that the emission bands observed in Figs. 1 and 2 are due to SiCl₄⁺ and GeCl₄⁺  $\tilde{C}$ - $\tilde{A}$ , $\tilde{X}$  transitions respectively, the large width of the bands being due to the repulsive nature of the  $\tilde{A}$  and  $\tilde{X}$  states. The fluorescence excitation functions obtained at Daresbury (Figs. 3 and 4) confirm this assignment.

The absence of the two broad bands with CCl₄, however, is surprising, since it is not obvious why CCl₄ should behave differently from SiCl₄/GeCl₄. There is the possibility that the agreement between the PE data for SiCl₄/GeCl₄ and the observed emission bands (Table II) is coincidental, and the emissions are due to a fragment which is produced by rapid dissociation of the  $\tilde{C}$  state of SiCl₄⁺/GeCl₄⁺. Although this seems unlikely, it is sensible to eliminate all fragments as emitters of the broad bands before their assignment to SiCl₄⁺/GeCl₄⁺  $\tilde{C}$ - $\tilde{A}$ , $\tilde{X}$  can be made definitive.

#### A. Emission from fragments of SiCl4

Besides SiCl₄⁺, the possible emitters of the 410 and 570 nm emission bands in Fig. 1 are the fragments SiCl_n and SiCl_n⁺ with n = 1-3. Since this spectrum is observed with neon metastables in the Penning ionization experiment, only fragments with dissociation energies below the Ne* recombination energy of 16.62 eV need be considered. From Table I, SiCl⁺ is immediately eliminated. If SiCl₂⁺ is the emitter, the photon energy corresponding to the band maximum must be added to the energy of the lowest channel to include SiCl₂⁺ (i.e., 15.2 eV) to produce the minimum energy for the dissociative fragmentation of SiCl₄ to excited SiCl₂⁺. For the 410 nm band ( $\equiv 3.0 \text{ eV}$ ) this minimum energy is 18.2 eV, higher than the Ne* recombination energy of 16.6 eV. The same is true for the 570 nm band. Therefore, the observed emissions cannot be due to SiCl₂⁺.

The possibility that the observed bands originate from neutral SiCl or  $SiCl_2$  (which are candidates on energetic

grounds) is also considered unlikely. SiCl has been comprehensively studied^{20,29,39,40} and no continuous emission bands have been assigned to low-lying states of this molecule. Moreover, none of the known discrete SiCl bands are observed in the electron impact spectrum on SiCl₄ (Fig. 1). Only one electronic transition in SiCl₂ has definitely been assigned, the  $\tilde{A} \, {}^{1}B_{1} - \tilde{X} \, {}^{1}A_{1}$  band system around 330 nm observed in both absorption⁴¹ and emission.⁴² This transition is between the two lowest energy states in SiCl₂, and therefore if this molecule is the emitter of the 410 and 570 nm bands, the transitions must be between highly excited electronic states. This is improbable. Furthermore, the  $\tilde{A} - \tilde{X}$  band system is not observed in the electron impact spectrum.

The only remaining possibilities are SiCl₃ and SiCl₃⁺, both possible on energetic grounds (Table I). No emission bands due to these free radicals are known. However, if either is the emitter of the 410 and 570 nm bands in Fig. 1, it might be expected that the same features be found in the spectra of electron impact on other SiCl₃-containing compounds. SiCl₃  $\cdot$  C₂H₅, SiCl₃  $\cdot$  CH₃, and SiCl₃  $\cdot$  H were therefore studied in the molecular beam/electron beam apparatus. With the first two compounds, no discrete or continuous bands are observed above the noise of the electron gun filament. With SiCl₃H broad continuous bands with maxima at 360, 475, and 590 nm are observed (the latter two heavily overlapped),³⁸ but the bands in Fig. 1 are not detected. It therefore seems very unlikely that the 410 and 570 nm bands are due to  $SiCl_3$  or  $SiCl_3^+$ . All the accumulative evidence is that they are due to SiCl₄⁺  $\tilde{C}$ - $\tilde{X}$ , $\tilde{A}$ .

#### B. Emission from fragments of GeCl⁺

Besides  $\text{GeCl}_4^+$ , the possible emitters of the 495 and 615 nm bands in Fig. 2 are the fragments  $\text{GeCl}_n$  and  $\text{GeCl}_n^+$  with n = 1-3. Since both bands are observed with Ne^{*} metastables in the Penning experiment, GeCl⁺ can be ruled out on energetic grounds (Table I), but  $GeCl_2^+$  is just possible. However, the synchrotron experiment (Fig. 4) shows that the fluorescence bands at 495 ( $\equiv$  2.5 eV) and 615 nm ( $\equiv$  2.0 eV) turn on at a threshold energy of 14.5 eV. Therefore, the ground state of the emitter must lie at an energy less than (14.5-2.5) or 12.0 eV. Thus GeCl₂⁺ can also be eliminated on energetic grounds, since the lowest dissociation channel involving ground state  $GeCl_2^+$  lies at 13.5 eV (Table I). There is strong circumstantial evidence to eliminate neutral GeCl and GeCl₂ as the emitters. Discrete electronic transitions in GeCl are well known,^{20,43} and no continuous emission bands have been assigned as originating from excited electronic states of this radical. Furthermore, none of the discrete GeCl bands are observed in the electron impact spectrum on GeCl₄. The  ${}^{3}B_{1} - {}^{1}A_{1}$  and  ${}^{1}B_{1} - {}^{1}A_{1}$  transitions in GeCl₂ have been observed, but only in absorption.^{44,45} If the emitter of the 495 and 615 nm bands is GeCl₂, then the transitions must be from highly excited electronic state(s). This seems improbable. Furthermore, neither of the two discrete GeCl₂ bands is seen in the electron impact spectrum of GeCl₄. Since the ground state of the emitting fragment must lie at an energy  $\leq 12.0 \text{ eV}$ , GeCl₃⁺ can probably be eliminated on energetic grounds also (Table I), although the value of

the GeCl₃ ionization potential (9.5 eV) comes from an appearance potential measurement of GeCl₃⁺ from GeCl₄²⁵ and not from a direct measurement; the energy of the GeCl₃⁺ + Cl dissociation channel at 12.3 eV is therefore only an upper limit. The electronic spectroscopy of the GeCl₃ (and GeCl₃⁺) free radical is unknown, and no experiments have been performed with other GeCl₃-containing compounds. As with SiCl₄, all the accumulative evidence is that the 495 and 615 nm bands in Fig. 2 are due to GeCl₄⁺  $\tilde{C}$ - $\tilde{X},\tilde{A}$ .

#### C. Rydberg structure in SiCl₄

The fluorescence function for SiCl₄ excited by VUV radiation (Fig. 3) shows structure between 16.5 and 18.1 eV, i.e., above the threshold energy for fluorescence. There is a discontinuity in the structure at 18.1 eV. An expansion of this part of the spectrum is shown in Fig. 5, and the peak positions are given in Table III. The peaks are assigned to transitions to Rydberg states of SiCl₄ lying above the  $\tilde{C}$  state ionization potential (15.1 eV) which converge to the  $\tilde{D}^2A_1$ state of the ion at 18.1 eV (Fig. 5). These states autoionize to the  $\tilde{C}$  state of SiCl₄⁺, and hence are observed in fluorescence. The term values can be fitted to the normal Rydberg equation:

$$v=v^{00}-\frac{R_H}{\left(n-\delta\right)^2},$$

where  $v^{00}$  is the IP limit (18.1 eV),  $R_H$  is the Rydberg constant (13.59 eV), *n* is the quantum number of the Rydberg electron, and  $\delta$  is the quantum defect. The first observed member of the series at 16.60 eV has  $(n - \delta)^2 = 9.1$  (column 2 of Table III), hence  $(n - \delta) \simeq 3.0$ . These states arise from promotion of an electron from the  $2a_1$  Si 3s-Cl  $3s/3p \sigma$ -bonding molecular orbital of SiCl₄ to a highly excited Rydberg orbital, and group theory shows that transitions to a *p* or *d* Rydberg orbital only are allowed. This state therefore is either the n = 4 level of a *p* Rydberg series (with  $\delta \simeq 1.0$ ), the n = 4 level of a *d* Rydberg series (with  $\delta \simeq 0$ ). It is unlikely that the first member of a *d* Rydberg series would have n = 3, since the valence orbitals of SiCl₄ involve Si 3s/3p with Cl 3s/3p. Second, *d* Rydberg states tend to have low quan-

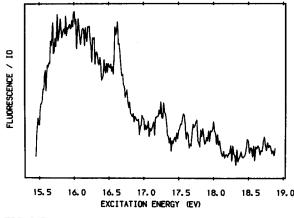


FIG. 5. Expansion of Fig. 3 in the range 15.5-19.0 eV.

TABLE III. Rydberg states of SiCl₄ converging to SiCl₄  $\tilde{D}^2A_1$ .

Energy (eV)	$\overline{R_H}/\nu^{00}-\nu^*$	$(n-\delta)_{approx}$	
16.60	9.1	3	
17.23	15.6		
17.30 \$	17.0 🕻	4	
17.56	25.2	5	
17.72	35.8	6	
17.83	50.3	7	

^a Calculated using  $v^{00} = 18.10 \text{ eV}$  (Ref. 12) and  $R_H = 13.59 \text{ eV}$ .

tum defects close to zero.^{46,47} Therefore, the most likely assignment is a p Rydberg series with  $n \ge 4$  and  $\delta \ge 1.0$ .

#### **VI. DISCUSSION**

We believe that the assignment of the broad bands in Figs. 1 and 2 to bound-free emission in  $SiCl_4^+/GeCl_4^+$  is almost definitive. The evidence is summarized below.

(1) The onset of the emission in both bands of SiCl₄/ GeCl₄ (Figs. 3 and 4) occurs at the adiabatic IP of the  $\tilde{C}$  state of the parent ion, i.e., 15.1 and 14.5 eV, respectively. The emission is therefore related to the initial formation of SiCl₄⁺/GeCl₄⁺  $\tilde{C}^2T_2$ .

(2) The sharp increase at the fluorescence thresholds suggests that the fluorescence is produced by a photoionization process. Similar observations have been made for  $N_2^+ B\,^2\Sigma_{\mu}^+$  at 18.7 eV,  $CO^+ B\,^2\Sigma^+$  at 19.7 eV,  $N_2O^+\widetilde{A}\,^2\Sigma^+$  at 16.4 eV,⁴⁸ and the  $\widetilde{C}\,^2T_2$  and  $\widetilde{D}\,^2A_1$  states of  $CF_4^+/SiF_4^+/GeF_4^{+}$ .⁴⁹ Fluorescence produced by a dissociative process is expected to show a smooth and slow increase at the threshold.⁵⁰

(3) The excitation cross section of a neutral process usually depends on both the excitation energy and the excitation source (photon, electron, or photoion). For an ionization process, however, as long as the excitation energy is sufficient, the dependence on excitation source is not critical. The results in Sec. IV indicate that the excitation is not dependent on the source, and this suggests that the emitting species are ions.

(4) Partial ionization cross sections for the  $2t_2$  molecular orbital of SiCl₄ have been measured as a function of excitation energy by angle-resolved photoelectron spectroscopy.⁵¹ Ionization from this orbital gives SiCl₄⁺  $\tilde{C}^2 T_2$ . The shape of the fluorescence excitation function in Fig. 3 is the same as for the partial ionization cross section of this molecular orbital (Fig. 5 of Ref. 51). Again, the relation of the 410, 570 nm emission bands to the initial formation of SiCl₄⁺  $\tilde{C}^2 T_2$  is confirmed.

(5) The excellent agreement of the observed emissions with photoelectron data for SiCl₄/GeCl₄ strongly suggests that the bands are due to SiCl₄⁺/GeCl₄⁺ $\tilde{C}-\tilde{A},\tilde{X}$ . On energetic grounds, the only ion which is an alternative possibility for the carrier of the 410, 570 nm bands in the silicon tetrachloride experiment is SiCl₃⁺. The synchrotron results mean that SiCl₄⁺ $\tilde{C}^2T_2$  would have to (pre)dissociate on a rapid time scale for this to be a possibility. Furthermore, the absence of these bands in the electron impact excitation of other SiCl₃containing compounds suggests that SiCl₃⁺ is not the emitter of the observed radiation. The assignment of the fluorescence to  $SiCl_4^+/GeCl_4^+ \tilde{C}^2 T_2$ , and the transitions to  $\tilde{C}-\tilde{A},\tilde{X}$  seems conclusive.

The main difference between the excited electronic states of the three fluorides  $CF_4^+/SiF_4^+/GeF_4^+$  and the three chlorides CCl₄⁺/SiCl₄⁺/GeCl₄⁺ is the decay properties of the  $\tilde{D}^2 A_1$  state. In MF₄⁺ fluorescence is observed from this state both to the bound  $\widetilde{C}$  state and the repulsive  $\widetilde{A}$  and  $\widetilde{X}$ states. In MCl₄⁺, however, fluorescence decay from  $\tilde{D}$  is not observed. The reason(s) for this difference is not yet explained. The  $\tilde{C}^2 T_2$  state of the fluorides and chlorides also show differing spectroscopic and dynamic behavior. SiF₄⁺ and GeF⁺₄  $\tilde{C}$  show dynamic Jahn–Teller distortion from  $T_d$ geometry,^{2,3} and do not decay by a radiative process.⁴⁹  $CF_4^+ \tilde{C}$  does not show Jahn-Teller distortion, ¹ yet this state decays radiatively to the  $\widetilde{A}$  and  $\widetilde{X}$  states via broad band  $\widetilde{C}$ - $\widetilde{A}, \widetilde{X}$  emission.⁷ This paper has established that SiCl₄⁺ and GeCl⁺  $\tilde{C}$  decay radiatively, but CCl⁺  $\tilde{C}$  does not, and it is tempting to speculate that there is a connection between the spectroscopic and dynamic decay properties of this state. It would be interesting, therefore, to observe the presence or absence of Jahn–Teller activity in the  $\tilde{C}^2 T_2$  state of CCl₄⁺,  $SiCl_4^+$ , and  $GeCl_4^+$ . This information would normally be observed in the  $\tilde{C}$  state photoelectron band, but at the low resolution of this technique no evidence for Jahn-Teller distortion can be observed.¹⁴ It is difficult otherwise to understand why  $CCl_{4}^{+}\widetilde{C}$  exhibits different dynamic properties from  $SiCl_4^+$  and  $GeCl_4^+ \tilde{C}$ . The broad band emission in Toyoda's experiment on  $CCl_4^{37}$  is almost certainly due to a neutral fragment ( $CCl_2$  or  $CCl_3$ ), and this would explain the unstructured background signal in our synchrotron experiment with  $CCl_4$  (Sec. IV).

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- ¹J. F. M. Aarts, S. M. Mason, and R. P. Tuckett, Mol. Phys. **60**, 761 (1987).
- ²S. M. Mason and R. P. Tuckett, Mol. Phys. 60, 771 (1987).
- ³S. M. Mason and R. P. Tuckett, Mol. Phys. 62, 979 (1987).
- ⁴C. R. Brundle, M. B. Robin, and H. Basch, J. Chem. Phys. 53, 2196 (1970).
- ⁵D. R. Lloyd and P. J. Roberts, J. Electron. Spectrosc. 7, 325 (1975).
- ⁶R. Jadrny, L. Karlsson, L. Mattsson, and K. Siegbahn, Chem. Phys. Lett. 49, 203 (1977).
- ⁷J. F. M. Aarts, Chem. Phys. Lett. **114**, 114 (1985).
- ⁸J. F. M. Aarts, Chem. Phys. 101, 105 (1986).
- ⁹H. van Lonkhuyzen and J. F. M. Aarts, Chem. Phys. Lett. 140, 434 (1987).
- ¹⁰S. M. Mason, R. P. Tuckett, and R. N. Dixon, Philos. Trans. R. Soc. London Ser. A 324, 289 (1988).
- ¹¹A. Carrington and R. P. Tuckett, Chem. Phys. Lett. 74, 19 (1980).

- ¹²P. J. Bassett and D. R. Lloyd, J. Chem. Soc. A 1971, 641.
- ¹³J. C. Green, M. L. H. Green, P. J. Joachim, A. F. Orchard, and D. W. Turner, Philos. Trans. R. Soc. London Ser. A 268, 111 (1970).
- ¹⁴R. G. Egdell, I. L. Fragala, and A. F. Orchard, J. Electron. Spectrosc. 17, 267 (1979).
- ¹⁵B. D. El-Issa and A. Hincliffe, J. Chem. Soc. Faraday Trans. 2 76, 1375 (1980).
- ¹⁶J. K. Zhu, D. Li, J. Li, and Y. K. Pan, Theor. Chim. Acta 63, 223 (1983).
- ¹⁷R. N. Dixon and R. P. Tuckett, Chem. Phys. Lett. 140, 553 (1987).
- ¹⁸H. van Lonkhuyzen and C. A. de Lange, Chem. Phys. 89, 313 (1984).
- ¹⁹C. E. Moore, Atomic Energy Levels, Natl. Stand. Ref. Data Ser., Natl.
- Bur. Stand. Circ. No. 467 (U. S. GPO, Washington, D. C., 1949), Vol. 1.
  ²⁰G. Herzberg and K. P. Huber, *Constants of Diatomic Molecules* (Van Nostrand Reinhold, New York 1979).
- ²¹W. von Niessen, L. Asbrink, and G. Bieri, J. Electron. Spectrosc. 26, 173 (1982).
- ²²JANAF Thermochemical Tables, Natl. Stand. Ref. Data Ser., Natl. Bur. Stand. Circ. No. 37 (U. S. GPO, Washington, D. C., 1971).
- ²³R. Walsh, Acc. Chem. Res. 14, 246 (1981).
- ²⁴J. Tamas, G. Czira, A. K. Maltsev, and O. M. Nefedov, J. Organometall. Chem. 40, 311 (1972).
- ²⁵O. Uy Manuel, D. W. Muenow, and J. L. Margrave, Trans. Faraday Soc. 65, 1296 (1969).
- ²⁶D. D. Wagman, W. H. Evans, V. B. Parker, I. Halow, S. M. Bailey, and R. H. Schumann, *Selected Values of Chemical Thermodynamic Properties*, U. S. Natl. Bur. Stand. Tech. Note (National Bureau of Standards, Washington, D. C., 1968).
- ²⁷J. W. Hepburn, D. J. Trevor, J. E. Pollard, D. A. Shirley, and Y. T. Lee, J. Chem. Phys. 76, 4287 (1982).
- ²⁸J. S. Shapiro and F. P. Lossing, J. Phys. Chem. 72, 1552 (1968).
- ²⁹G. Bosser, H. Bredohl, and I. Dubois, J. Mol. Spectrosc. **106**, 72 (1984).
  ³⁰H. Bock, B. Solouki, and G. Maier, Ang. Chemie Int. Ed. Eng. **24**, 205 (1985).
- ³¹F. Melen and I. Dubois, J. Mol. Spectrosc. 124, 476 (1987).

- ³²G. Jonkers, S. M. Van der Kerk, and C. A. de Lange, Chem. Phys. 70, 69 (1982).
- ³³J. B. Farmer, H. S. Henderson, F. P. Lossing, and D. G. H. Marsden, J. Chem. Phys. 24, 348 (1956).
- ³⁴W. C. Steele, L. D. Nichols, and F. G. A. Stone, J. Am. Chem. Soc. 84, 4441 (1962).
- ³⁵Eight Peak Index of Mass Spectra (HMSO, London, 1970).
- ³⁶H. van Lonkhuyzen and J. F. M. Aarts (private communication).
- ³⁷M. Toyoda, T. Ogawa, and N. Ishibashi, Nippon Kagaku Kaishi 8, 1077 (1977).
- ³⁸S. M. Mason, Ph.D. thesis, University of Cambridge, 1988.
- ³⁹F. Melen, Y. Houbrects, I. Dubois, B. Le Huyen, and H. Bredohl, J. Phys. B 14, 3637 (1981).
- ⁴⁰B. P. Ruzsicska, A. Jodhan, I. Safarik, O. P. Strauss, and T. N. Bell, Chem. Phys. Lett. **113**, 67 (1985).
- ⁴¹M. Suzuki, N. Washida, and G. Inoue, Chem. Phys. Lett. 131, 24 (1986).
- ⁴²D. Sameith, J. P. Monch, H. J. Tiller, and K. Schade, Chem. Phys. Lett. 128, 483 (1986).
- ⁴³R. W. B. Pearse and A. G. Gaydon, *The Identification of Molecular Spectra*, 4th ed. (Chapman and Hall, London, 1976).
- 44A. Tewarson and H. B. Palmer, J. Mol. Spectrosc. 22, 117 (1967).
- ⁴⁵J. W. Hastie, R. H. Hauge, and J. L. Margrave, J. Mol. Spectrosc. 29, 152 (1969).
- ⁴⁶G. Herzberg, *Electronic Spectra of Polyatomic Molecules* (Van Nostrand Reinhold, New York, 1966), p. 340.
- ⁴⁷J. W. Rabalais, *Principles of UV Photoelectron Spectroscopy* (Wiley, New York, 1977), p. 367.
- ⁴⁸L. C. Lee, J. Phys. B 10, 3033 (1977).
- ⁴⁹I. R. Lambert, S. M. Mason, R. P. Tuckett, and A. Hopkirk, J. Chem. Phys. 89, 2683 (1988).
- ⁵⁰L. C. Lee, X. Wang, and M. Suto, J. Chem. Phys. 85, 6294 (1986).
- ⁵¹T. A. Carlson, A. Fahlman, M. O. Krause, T. A. Whitley, F. A. Grimm, M. N. Piancastelli, and J. W. Taylor, J. Chem. Phys. 84, 641 (1986).